

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims**

1. (Currently Amended) A semiconductor device, comprising:  
a polysilicon gate electrode provided on a silicon substrate not including SiGe,  
wherein  
said polysilicon gate electrode is subjected to compressive stress as internal stress therein, to apply tensile stress to said silicon substrate, and  
ions having a mass number of 70 or more are implanted into said polysilicon gate electrode.
2. (Currently Amended) The semiconductor device according to claim 1, wherein  
said polysilicon gate electrode is a gate electrode of an n-channel MOS transistor.
3. (Original) The semiconductor device according to claim 2, wherein  
said ions having a mass number of 70 or more are operative to serve as those for forming a source and drain region of said n-channel MOS transistor.
4. (Original) The semiconductor device according to claim 1, wherein  
said ions having a mass number of 70 or more are electrically inactive ions.
5. (Currently Amended) The semiconductor device according to claim 1, wherein  
said polysilicon gate electrode has a bird's beak at a lower edge portion thereof, said bird's beak being defined by a silicon oxide film.

6. (Original) The semiconductor device according to claim 1, wherein said silicon substrate is a strained silicon substrate.

7-18 (Cancelled).